IN THE CLAIMS

1-18. (Canceled)

19. (Currently amended) A method of making a semiconductor substrate ~~according to Claim 18,~~ comprising:

forming a variant impurity layer with an impurity concentration varying in a depth direction on one surface of a supporting substrate by means other than anodic oxidation, wherein a variant impurity layer including at least two sublayers having different impurity concentrations is formed in said variant layer forming step; and

forming a porous layer by providing pores in the variant impurity layer by anodic oxidation so that a porosity in the porous layer varies in the depth direction, ~~and~~ wherein a porous layer including at least two sublayers having different porosities is formed in said porous layer forming step.

20. (Previously presented) A method of making a semiconductor substrate according to Claim 19, wherein at least two sublayers having different impurity concentrations are formed on one surface of the supporting substrate in said variant layer forming step.

21. (Previously presented) A method of making a semiconductor substrate according to Claim 19, wherein, in said variant layer forming step, a growth layer is deposited on one surface of the supporting substrate, and then an impurity is diffused into the growth layer so as to form at least two sublayers having different impurity concentrations.

22. (Canceled)

23. (Currently amended) A method of making a semiconductor substrate ~~according to claim 18~~comprising:

forming a variant impurity layer with an impurity concentration varying in a depth direction on one surface of a supporting substrate by means other than anodic

oxidation, wherein, in said variant layer forming step, a low-impurity sublayer comprising a semiconductor having a low impurity concentration is formed and a high-impurity sublayer comprising a semiconductor having a high impurity concentration is formed on the surface, away from the supporting substrate, of the low-impurity sublayer; and

forming a porous layer by providing pores in the variant impurity layer by anodic oxidation so that a porosity in the porous layer varies in the depth direction.

24. (Previously presented) A method of making a semiconductor substrate according to claim 23, wherein, in said variant layer forming step, each of said supporting substrate and said variant impurity layer comprises p-type silicon containing a p-type impurity, the low-impurity sublayer has a p-type impurity concentration of 1×10^{19} cm $^{-3}$ or more, and the high-impurity sublayer has a p-type impurity concentration of less than 1×10^{19} cm $^{-3}$.

25. (Canceled)

26. (Currently amended) A method of making a semiconductor substrate ~~according to claim 18, further comprising a step for~~ comprising:

forming a variant impurity layer with an impurity concentration varying in a depth direction on one surface of a supporting substrate by means other than anodic oxidation;

forming a porous layer by providing pores in the variant impurity layer by anodic oxidation so that a porosity in the porous layer varies in the depth direction; and

forming a semiconductive thin film on the surface, away from the supporting substrate, of the porous layer.

27. (Previously presented) A method of making a semiconductor substrate

according to claim 26, wherein said semiconductive thin film is formed of a single crystal provided by epitaxial growth.

28. (Currently amended) A method of making a semiconductor substrate according to claim 26, wherein said semiconductive thin film comprises a semiconductor selected from the group consisting of a semiconductor containing at least one of silicon and germanium, a semiconductor containing gallium and arsenic, ~~and~~ a semiconductor containing gallium and phosphorus, and a semiconductor containing gallium and nitrogen.

29. (Currently Amended) A method of making a semiconductor substrate ~~according to claim 18, further comprising a heating step of~~ comprising:

forming a variant impurity layer with an impurity concentration varying in a depth direction on one surface of a supporting substrate by means other than anodic oxidation;

forming a porous layer by providing pores in the variant impurity layer by anodic oxidation so that a porosity in the porous layer varies in the depth direction; and

heating the porous layer for recrystallization.

30. (Canceled).

31. (Currently Amended) A method of making a semiconductor substrate ~~according to claim 30~~ comprising:

forming a high-impurity layer comprising a semiconductor having an impurity concentration of $1x10^{18}$ cm $^{-3}$ or more on one surface of a supporting substrate by means other than anodic oxidation, wherein in said high-impurity layer forming step, the high-impurity layer is formed by epitaxial growth; and

forming pores in the high-impurity layer by anodic oxidation to form a porous layer having different porosities in a depth direction.

32. (Previously presented) A method of making a thin-film semiconductive member comprising:

forming a variant impurity layer with an impurity concentration varying in a depth direction on one surface of a supporting substrate by means other than anodic oxidation;

forming a porous layer by providing pores in the variant impurity layer by anodic oxidation so that a porosity in the porous layer varies in a depth direction;

forming a semiconductive thin film on the surface, away from the supporting substrate, of the porous layer; and

separating the semiconductive thin film from the supporting substrate by cleavage in a porous phase.

33. (Previously presented) A method of making a thin-film semiconductive member comprising:

forming a high-impurity layer comprising a semiconductor having an impurity concentration of $1x10^{18}$ cm $^{-3}$ or more on one surface of a supporting substrate by means other than anodic oxidation;

forming pores in the high-impurity layer by anodic oxidation to form a porous layer having different porosities in a depth direction;

forming a semiconductive thin film on the surface, away from the supporting substrate, of the porous layer; and

separating the semiconductive thin film from the supporting substrate by cleavage in a porous phase.